



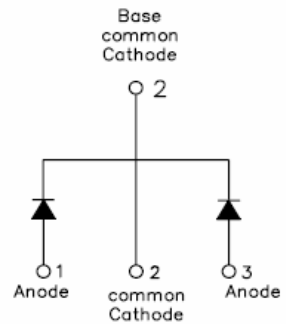
## SBR10100CT SCHOTTKY RECTIFIER

### Applications:

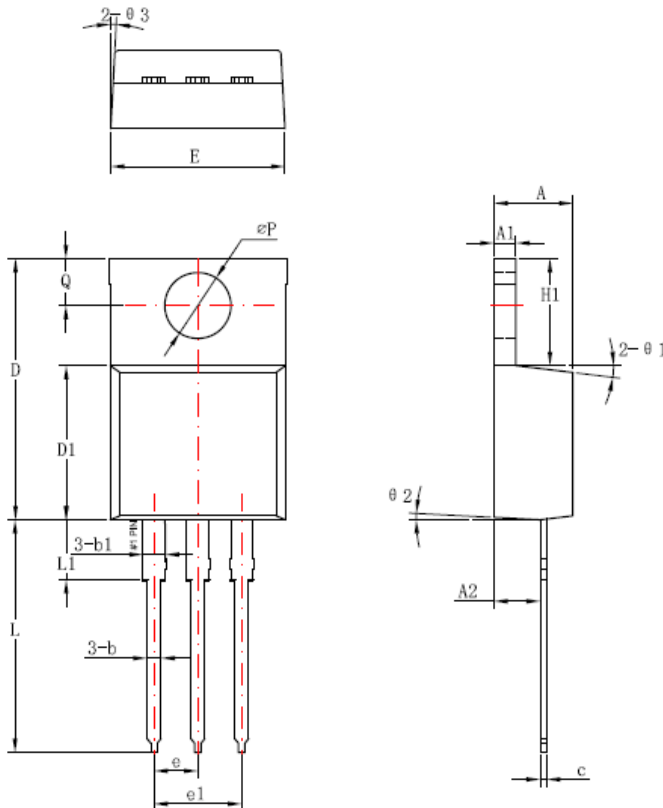
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### Features:

- 150°C TJ operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

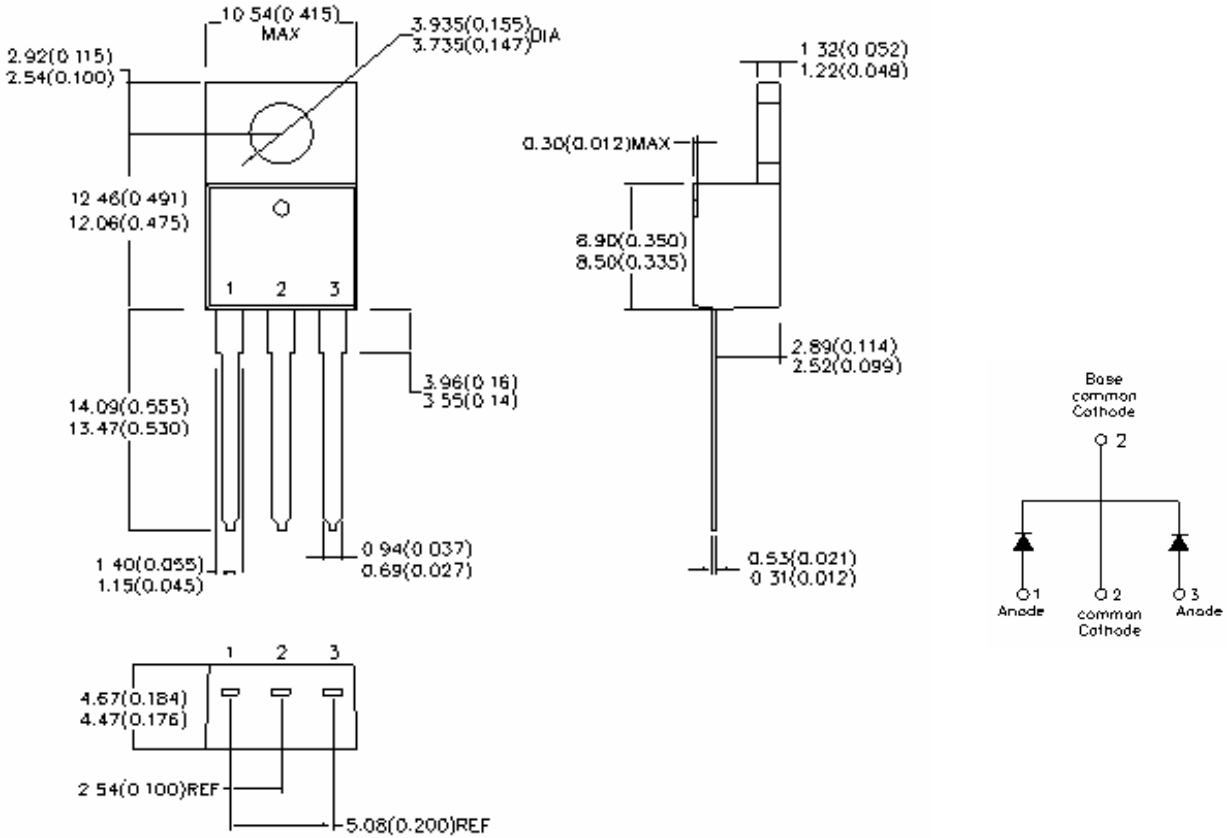


### Mechanical Dimensions (In mm / Inches) and Marking:



Symbol	Dimensions in millimeters		
	Min	Typical	Max
A	4.42	4.57	4.72
A1	1.17	1.27	1.37
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
D	14.94	15.24	15.54
D1	8.85	9.00	9.15
E	10.01	10.16	10.31
e		2.54	
e1		5.06	
H1	6.04	6.24	6.44
L	12.7	13.56	13.78
L1		3.5	
ΦP	3.74	3.84	4.04
Q	2.54	2.74	2.94
Θ1		7°	
Θ2		3°	
Θ3		4°	

### OPTION1 (HD)

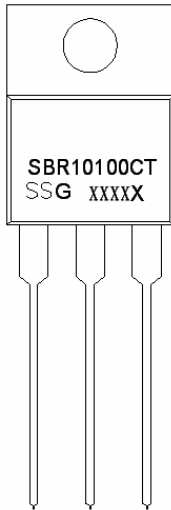


**OPTION2 (CJ)**

**TO-220AB**



**Marking Diagram:**



Where XXXXX is YYWWL

- SBR = Device Type
- 10 = Forward Current (10A)
- 100 = Reverse Voltage (100V)
- CT = Configuration
- SSG = SSG
- YY = Year
- WW = Week
- L = Lot Number

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

**Ordering Information:**

Device	Package	Shipping
SBR10100CT	TO-220AB (Pb-Free)	50 pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

**Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	100	V
Max. Average Forward	$I_{F(AV)}$	50% duty cycle @ $T_C = 150^\circ C$ , rectangular wave form	10	A
Max. Peak One Cycle Non-Repetitive Surge Current (per leg)	$I_{FSM}$	Surge applied at rated load conditions halfwave, single phase,60Hz	120	A



**Electrical Characteristics:**

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg) *	$V_{F1}$	@ 5 A, Pulse, $T_C = 25\text{ }^\circ\text{C}$	0.88	V
	$V_{F2}$	@ 5 A, Pulse, $T_C = 125\text{ }^\circ\text{C}$	0.75	V
Max. Reverse Current (per leg) *	$I_{R1}$	@ $V_R = \text{rated } V_R$ $T_C = 25\text{ }^\circ\text{C}$	1.0	mA
	$I_{R2}$	@ $V_R = \text{rated } V_R$ $T_C = 125\text{ }^\circ\text{C}$	15.0	mA
Repetitive peak reverse current	$I_{RRM}$	$t_p = 2\text{ }\mu\text{s}$ square F= 1 kHz	1	A
Non-Repetitive Avalanche Energy	$E_{AS}$	$T_J = 25\text{ }^\circ\text{C}$ , $I_{AS} = 5\text{ A}$ , $L = 1\text{ mH}$	12.5	mJ
Max. Junction Capacitance (per leg)	$C_T$	@ $V_R = 5\text{ V}$ , $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{ MHz}$	300	pF
Max. Voltage Rate of Change	dv/dt	-	10,000	V/ $\mu\text{s}$

\* Pulse Width < 300 $\mu\text{s}$ , Duty Cycle <2%

**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	$T_J$	-	-55 to +200	$^\circ\text{C}$
Max. Storage Temperature	$T_{stg}$	-	-55 to +150	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	3.5	$^\circ\text{C/W}$
Approximate Weight	wt	-	2	g
Case Style		TO-220AB		

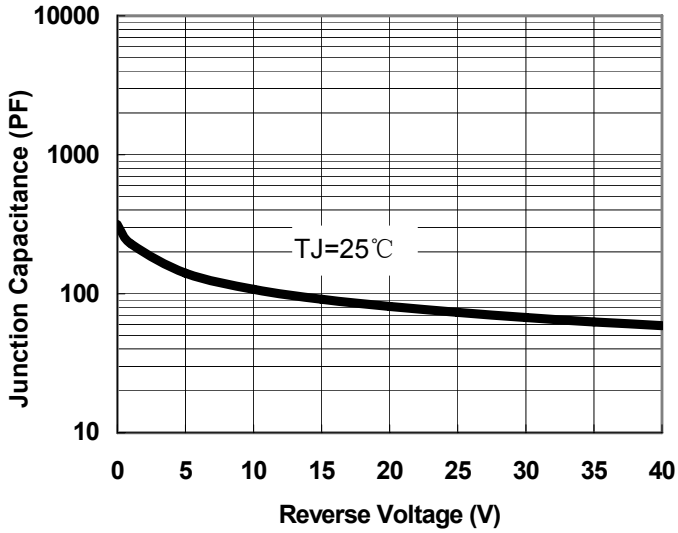


Fig.1-Typical Junction Capacitance

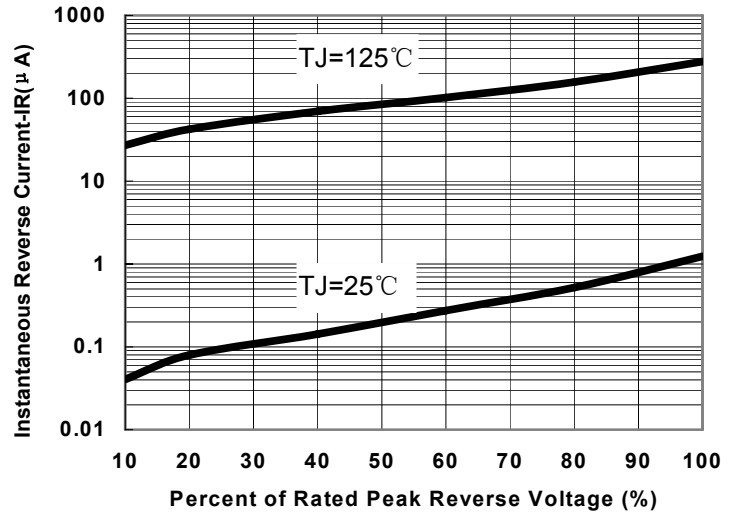


Fig.2-Typical Reverse Characteristics

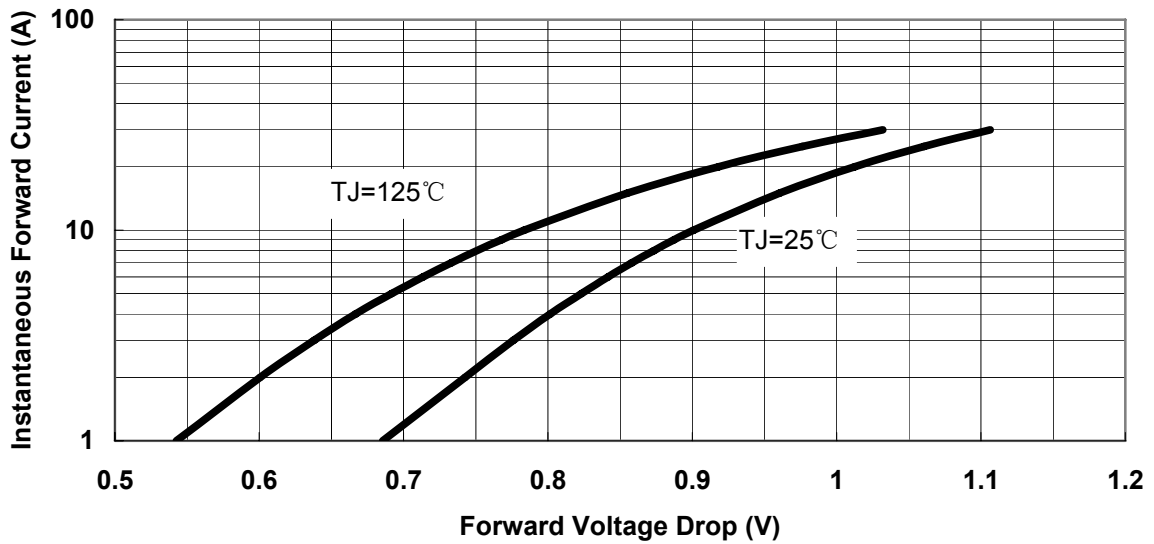


Fig.3-Typical Instantaneous Forward Voltage Characteristics



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